onsemi

Current-Shunt Monitors, Zero-Drift, 40 V Common Mode, Bidirectional, Shutdown

NCS21671, NCV21671

The NCS21671 and NCV21671 are a series of voltage output current sense amplifiers offered in gains of 25, 50, 100, and 200 V/V. These parts can measure voltage across shunts at common mode voltages from -0.1 V to 40 V, independent of supply voltage. The low offset of the zero-drift architecture enables current sensing with voltage drops across sense resistors as low as 10 mV full-scale. An optional enable function is available to reduce current drain through the input pins and power supply pins to negligible levels when disabled or if Vs is less than 1.5 V. Two optional pins are included to simplify input filtering. These devices can operate from a single +1.8 V to +5.5 V power supply, drawing a maximum of 80 μ A of supply current. These parts are available in Micro10 and SC70–6 packages.

Features

- Wide Common Mode Input Range: -0.1 V to 40 V
- Supply Voltage Range: 1.8 V to 5.5 V
- Low Offset Voltage: ±25 µV max
- Rail-to-Rail Output Capability
- Low Current Consumption: 80 µA max
- Enable Pin to Turn Off Input and Power Supply Currents
- Optional Input Filtering Through C_{IN+} and C_{IN-} Pins
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- Power Bus Monitoring
- Battery Current Monitor
- Lighting Ballast



Micro10 CASE 846B-03

MARKING DIAGRAMS



XXXX = Device Code A = Assembly Location

Y

W

= Year

= Work Week

O

= Pb-Free Package



SC-88/SC70-6 /SOT-363 CASE 419B-02 XXX = Specific Device Code M = Date Code* = Pb-Free Package

XXXM=

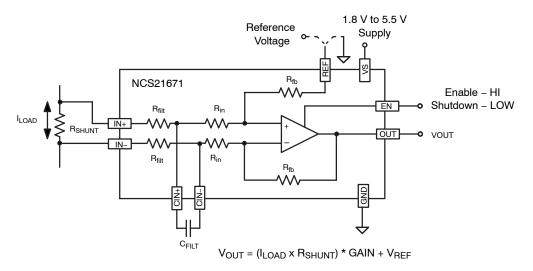
(Note: Microdot may be in either location)

PIN CONNECTIONS

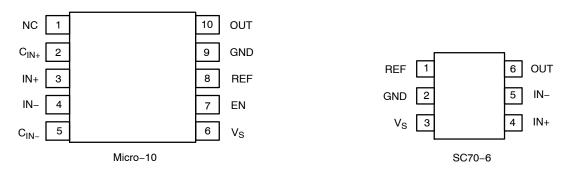
See pin connections on page 2 of this datasheet.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 14 of this data sheet.









PIN DESCRIPTION

PIN FUNCTION DESCRIPTION

| Pin Name | Туре | Description |
|------------------|------------|--|
| NC | No connect | This pin must be left not connected to external circuitry. |
| C _{IN+} | Input | Available on Micro10 packages only. An optional capacitor can be added between $\rm C_{IN+}$ and $\rm C_{IN-}$ to create a low-pass input filter. |
| IN+ | Input | This pin is connected to the positive side of the sense resistor or current shunt. This pin becomes high impedance when the part is in shutdown mode (EN = 0). |
| IN- | Input | This pin is connected to the negative side of the sense resistor or current shunt. This pin becomes high impedance when the part is in shutdown mode (EN = 0). |
| C _{IN-} | Input | Available on Micro10 packages only. An optional capacitor can be added between $C_{\rm IN+}$ and $C_{\rm IN-}$ to create a low-pass input filter. |
| Vs | Supply | This is the positive supply pin that provides power to the internal circuitry. An external bypass capacitor of 0.1 μF is recommended to be placed as close as possible to this pin. |
| EN | Input | Available on Micro10 packages only. There is no pull-up enable the part when this pin is open circuit. The enable pin can be connected to V_S or driven with a logic level to enable the part. If this pin is driven low the part enters a low power mode to conserve current consumption. |
| REF | Input | This pin sets the reference voltage of the internal difference amplifier circuit, allowing for unidiretional or bidirectional current sensing. For unidirectional current sensing, connect this pin to GND. For bidirectional current sensing, connect this pin between the GND and V_S range. |
| GND | Supply | This is the negative supply rail of the circuit. |
| OUT | Output | The output pin provides a low impedance voltage output. This pin becomes high impedance when the part is in shutdown mode (EN = 0). |

MAXIMUM RATINGS

| | Parameter | Symbol | Rating | Unit |
|--|----------------------|---------------------|-----------------------------------|------|
| Supply Voltage (Note 1) | | V _S | –0.3 to 6 | V |
| IN+, IN-, CIN+, CIN- Differential $(V_{IN+}) - (V_{IN-})$ (Note 2) | | $V_{IN+,}V_{IN-}$ | 44 | V |
| | Common-Mode (Note 2) | 1 [| –0.3 to +44 | |
| REF Input | | V _{REF} | GND-0.3 to (V _s) +0.3 | V |
| EN Input | | V _{EN} | GND-0.3 to (V _s) +0.3 | V |
| Output (Note 2) | | V _{OUT} | GND-0.3 to (V _s) +0.3 | V |
| Input Current into Any Pin | i (Note 2) | l _{IN} | ±10 | mA |
| Operating Temperature | | T _A | -40 to +150 | °C |
| Storage Temperature | | T _{STG} | -65 to +150 | °C |
| Junction Temperature | | T _{J(max)} | +150 | °C |
| ESD Capability, Human B | ody Model (Note 3) | HBM | ±2000 | V |
| Charged Device Model (Note 3) | | CDM | ±1000 | V |
| Latch-up Current (Note 4 |) | | ±100 | mA |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1. Refer to ELECTRICAL CHARACTERISTICS, RECOMMENDED OPERATING RANGES and/or APPLICATION INFORMATION for safe

 Refer to ELECTRICAL CHARACTERISTICS, RECOMMENDED OPERATING RANGES and/or APPLICATION INFORMATION for safe operating parameters.

2. Input voltage at any pin may exceed the voltage shown if current at that pin is limited to ±10 mA.

 This device series incorporates ESD protection and is tested by the following methods: ESD Human Body Model tested per JEDEC standard JS-001-2017

ESD Charged Device Model tested per JEDEC standard JS-001-2017

4. Latch-up Current tested per JEDEC standard JESD78E

THERMAL CHARACTERISTICS

| Parameter | Symbol | Micro10 / MSOP10 | SC88 / SC70-6 / SOT-363 | Unit |
|---|---------------------------|------------------|-------------------------|------|
| Junction-to-ambient thermal resistance (Notes 5, 6) | θ_{JA} | 180 | 188 | °C/W |
| Junction-to-case thermal resistance (Notes 5, 6) | $\theta_{\text{JC(top)}}$ | 71 | 128 | °C/W |
| Junction-to-top thermal characterization (Notes 5, 6) | Ψ_{JT} | 1.6 | 21 | °C/W |
| Junction-to-board thermal characterization (Notes 5, 6) | Ψ_{JB} | 98 | 91 | °C/W |

 Refer to ELECTRICAL CHARACTERISTICS, RECOMMENDED OPERATING RANGES and/or APPLICATION INFORMATION for safe operating parameters.

6. Values based on copper area of 645 mm² (or 1 in²) of 1 oz copper thickness and FR4 PCB substrate. (reference JESD51).

RECOMMENDED OPERATING RANGES

| Parameter | Symbol | Conditions | Min | Max | Unit |
|---------------------------|-----------------|------------------------|------|-----|------|
| Operating Temperature | T _A | NCS prefix | -40 | 125 | °C |
| | | NCV prefix | -40 | 125 | |
| Common Mode Input Voltage | V _{CM} | Full temperature range | -0.1 | 40 | V |
| Supply Voltage | V _S | Full temperature range | 1.8 | 5.5 | V |

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

ELECTRICAL CHARACTERISTICS At $T_A = +25^{\circ}C$, $V_{SENSE} = (V_{IN+}) - (V_{IN-})$; $V_S = 1.8 \text{ V}$ to 5.5 V, $V_{IN+} = 12 \text{ V}$, and $V_{REF} = V_S/2$, unless otherwise noted. **Boldface** limits apply over the specified temperature range, $T_A = -40^{\circ}C$ to $125^{\circ}C$.

| Parameter | Symbol | Conditions | | Min | Тур | Max | Unit |
|---|---|--|--------------------------|-----|-------|------|-------|
| INPUT | | | | | | | |
| Common Mode Rejection | CMRR | $V_{IN+} = -0.1 V \text{ to } 40 V,$ | G = 25 | 109 | 127 | - | dB |
| Ratio, RTI (Note 7) | | V _{SENSE} = 0 mV T _A = -40 °C to 125 °C | G = 50 | 109 | 127 | - | |
| | | | G = 100 | 109 | 134 | - | |
| | | | G = 200 | 109 | 134 | - | |
| Input Offset Voltage, | V _{OS} | V _{SENSE} = 0 mV | G = 25 | - | ±9 | ±19 | μV |
| RTI (Note 7) | | | G = 50 | - | ±4 | ±12 | |
| | | | G = 100 | - | ±3 | ±10 | |
| | | | G = 200 | - | ±2 | ±10 | |
| | | $V_{IN+} = -0.1 V \text{ to } 40 V$ | G = 25 | - | ±1 | ±60 | μV |
| | | V _{SENSE} = 0 mV | G = 50 | - | ±1 | ±40 | |
| | | | G = 100 | - | ±1 | ±25 | |
| | | | G = 200 | - | ±1 | ±25 | |
| Input Offset Voltage Drift vs. Temperature, RTI (Note 7) | $\mathrm{DV}_{\mathrm{OS}}/\mathrm{dT}$ | V _{SENSE} = 0 mV | | - | ±0.1 | ±0.5 | μV/°C |
| Power Supply Rejection Ratio | PSRR | V_{S} = 1.8 V to 5.5 V, V _{SENSE} = 0mV | | _ | ±1.0 | ±10 | μV/V |
| Input Bias Current | I _{IB} | V _{SENSE} = 0 mV | | - | 29 | 35 | μΑ |
| Input Bias Current in Shutdown (Note 10) | I _{IBSD} | V _{SENSE} = 0mV | V _{SENSE} = 0mV | | | 140 | nA |
| Input Bias Current in Shutdown (Note 10) | I _{IBSD} | $T_A = -40 \ ^\circ C$ to 125 $^\circ C$ | | - | - | 500 | nA |
| Input Offset Current | I _{IO} | V _{SENSE} = 0 mV | | - | ±0.3 | - | μΑ |
| Enable Input Threshold Voltage | V _{th(EN)} | Enabled | | 1.4 | - | - | V |
| | | Disabled | | - | - | 0.3 | |
| Enable Input Leakage Current | I _{EN} | $V_{EN} = V_S$ | | - | 3 | - | nA |
| | | V _{EN} = GND | | - | -3 | - | |
| Enable Time (Note 8) | t _{ON} | $R_L = 10 \text{ k}\Omega \text{ to GND}$ | | - | 65 | - | μs |
| Shutdown Time (Note 8) | t _{OFF} | $R_L = 10 \text{ k}\Omega \text{ to GND}$ | | - | 20 | - | μs |
| OUTPUT | | | | | | | |
| Gain | G | | G = 25 | - | 25 | - | V/V |
| | | | G = 50 | - | 50 | - | |
| | | | G = 100 | - | 100 | - | |
| | | | G = 200 | - | 200 | - | 1 |
| Gain Error | E _G | $V_{SENSE} = -5 \text{ mV to} + 5 \text{ mV},$ $T_A = -40^{\circ}\text{C} \text{ to} 125^{\circ}\text{C}$ | G = 25 | - | - | ±0.4 | % |
| | | $I_{A} = -40^{\circ}C$ to $125^{\circ}C$ | G = 50 | - | - | ±0.4 | |
| | | | G = 100 | - | - | ±0.3 | |
| | | G = 200 | | - | - | ±0.5 | |
| Nonlinearity Error | | | | - | ±0.01 | - | % |
| Reference Voltage Rejection | RVRR | $V_{\text{REF}} = 100 \text{ mV to}$ | G = 25 | - | - | 27 | μV/V |
| Ratio (Note 10) | | $(V_{S}^{-} - 100 \text{ mV})$ T _A = -40°C to 125°C | G = 50 | - | - | 15 |] |
| | | $V_{\rm S} = 5.5 \text{ V}$ | G = 100 | - | - | 10 | 1 |
| | | | G = 200 | - | - | 10 | 1 |
| Maximum Capacitive Load | CL | No sustained oscillation | | - | 1 | - | nF |

ELECTRICAL CHARACTERISTICS

At $T_A = +25^{\circ}$ C, $V_{SENSE} = (V_{IN+}) - (V_{IN-})$; $V_S = 1.8$ V to 5.5 V, $V_{IN+} = 12$ V, and $V_{REF} = V_S/2$, unless otherwise noted. **Boldface** limits apply over the specified temperature range, $T_A = -40^{\circ}$ C to 125 °C.

| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|-------------------------|-----------------|---|-----|--------------------|--------------------|------|
| VOLTAGE OUTPUT | | | | | | |
| Swing to VS Supply Rail | V _{OH} | | - | V _S –20 | V _S -35 | mV |
| Swing to GND | V _{OL} | $R_L = 10 \text{ k}\Omega \text{ to GND}$ $T_A = -40^{\circ}\text{C to } +125^{\circ}\text{C}$ | - | 1 | 2.5 | mV |

FREQUENCY RESPONSE

| Bandwidth (f _{-3dB}) | BW | C _L = 10pF | G = 25 | - | 40 | _ | kHz |
|--------------------------------|----------------|--------------------------------------|------------|---|-----|---|------|
| | | | G = 50 | - | 40 | - | |
| | | | G = 100 | - | 35 | - | |
| | | | G = 200 | - | 20 | - | |
| Slew Rate | SR | V _S = 5.5 V | | - | 0.3 | - | V/µs |
| Settling Time | Τ _S | From current step to within 19 value | % of final | - | 30 | - | μs |

NOISE

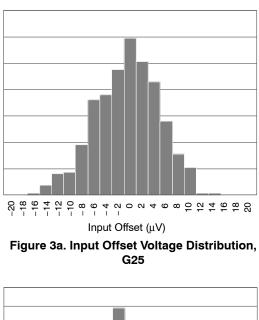
| Voltage Noise Density, | e _n | G = 25 | - | 56 | - | nV/√Hz |
|------------------------|----------------|---------|---|----|---|--------|
| RTI (Note 7) | | G = 50 | - | 46 | 1 | |
| | | G = 100 | - | 46 | - | |
| | | G = 200 | - | 46 | - | |

POWER SUPPLY

| Quiescent Current | IQ | V _{SENSE} = 0 mV | - | 45 | 80 | μA |
|-------------------------------|------------------|---------------------------|---|-----|-----|----|
| Quiescent Current in Shutdown | I _{QSD} | V _{SENSE} = 0 mV | - | 0.2 | 0.5 | μA |
| Power-on Time (Note 9) | t _{PON} | V _{SENSE} = 0 mV | - | 40 | - | μs |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
Referred to input.
Shutdown Time (t_{OFF}) and Enable Time (t_{ON}) are defined as the time between the 50% point of the signal applied to the EN pin and the point at which the output voltage reaches within 10% of its final value. V_{SENSE} = (0.75 * V_S - V_{REF}) / Gain.
Time between V_S is application and Vout reaching 10% of final value.
Guaranteed by characterization and/or design.

TYPICAL CHARACTERISTICS (At $T_A = +25^{\circ}C$, $V_{SENSE} = (V_{IN+}) - (V_{IN-})$.; $V_S = V_{EN} = 1.8$ V, $V_{REF} = V_S/2$, $V_{CM} = 12$ V, and all gains unless otherwise noted.)



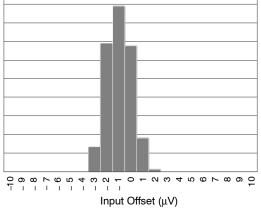
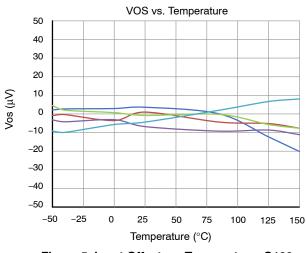
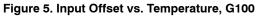


Figure 3c. Input Offset Voltage Distribution, G100





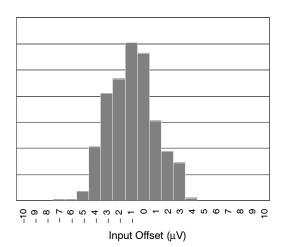


Figure 3b. Input Offset Voltage Distribution, G50

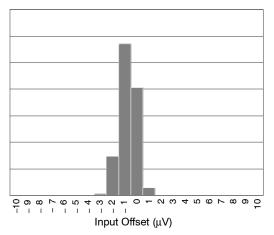
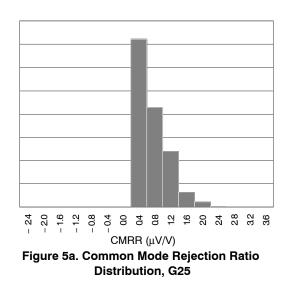
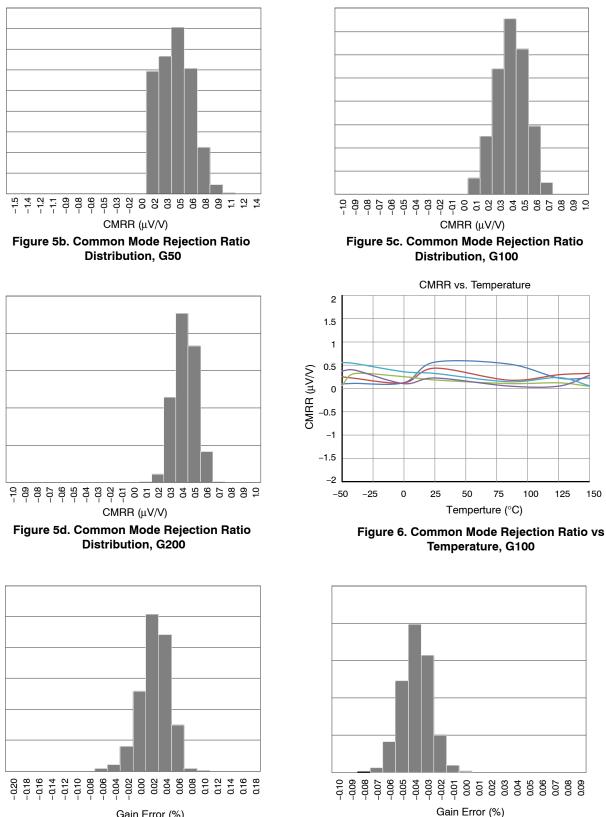


Figure 3d. Input Offset Voltage Distribution, G200

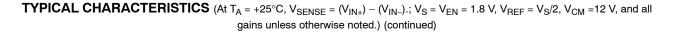


TYPICAL CHARACTERISTICS (At $T_A = +25^{\circ}C$, $V_{SENSE} = (V_{IN+}) - (V_{IN-})$; $V_S = V_{EN} = 1.8$ V, $V_{REF} = V_S/2$, $V_{CM} = 12$ V, and all gains unless otherwise noted.) (continued)



Gain Error (%) Figure 7a. Gain Error Distribution, G25

Figure 7b. Gain Error Distribution, G50



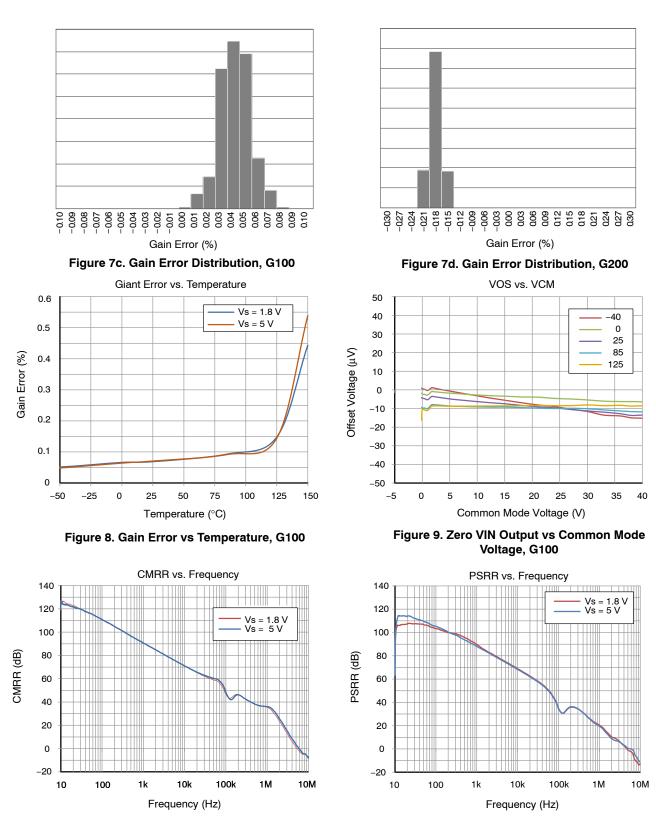


Figure 10. Common Mode Rejection Ratio vs Frequency, G100

Figure 11. Power Supply Rejection Ratio vs Frequency, G100

TYPICAL CHARACTERISTICS (At $T_A = +25^{\circ}C$, $V_{SENSE} = (V_{IN+}) - (V_{IN-})$.; $V_S = V_{EN} = 1.8$ V, $V_{REF} = V_S/2$, $V_{CM} = 12$ V, and all gains unless otherwise noted.) (continued)

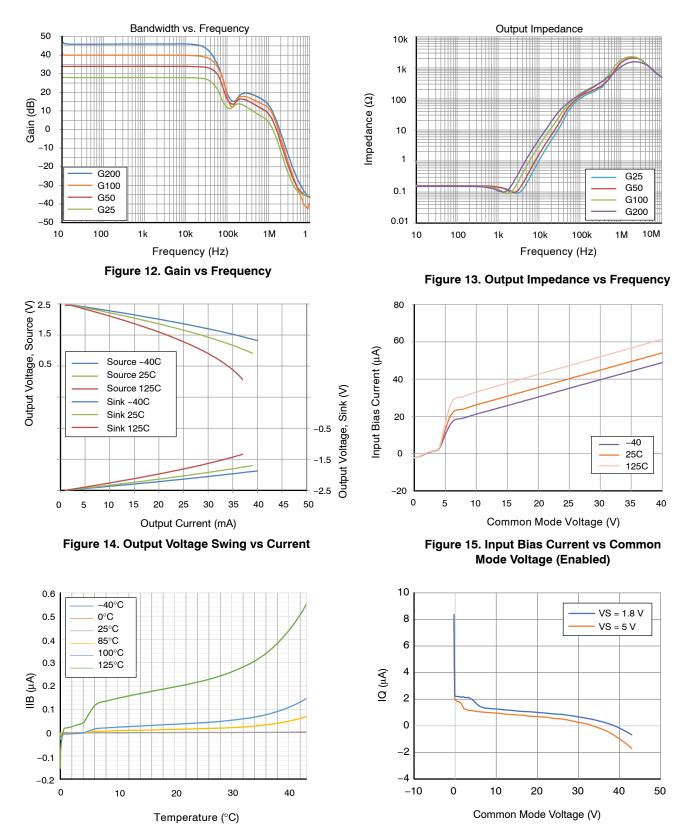




Figure 17. Quiescent Current vs Common Mode Voltage (Enabled)

TYPICAL CHARACTERISTICS (At $T_A = +25^{\circ}C$, $V_{SENSE} = (V_{IN+}) - (V_{IN-})$.; $V_S = V_{EN} = 1.8$ V, $V_{REF} = V_S/2$, $V_{CM} = 12$ V, and all gains unless otherwise noted.) (continued)

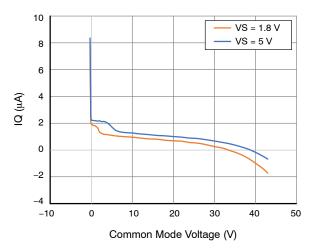


Figure 18. Quiescent Current vs Common Mode Voltage (Disabled)

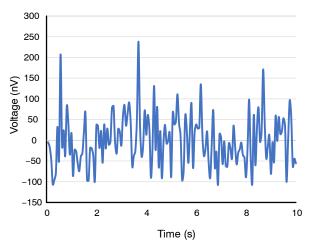
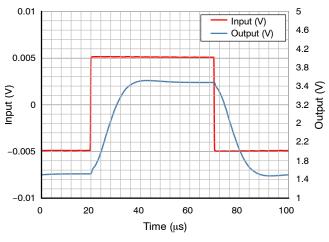


Figure 20. 0.1–Hz to 10–Hz Voltage Noise (Referred–To–Input)





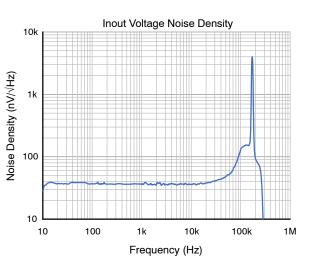


Figure 19. Voltage Noise Density (Referred-to-Input)

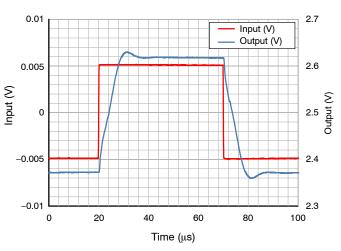


Figure 21. Step Response, G25 (10mV Input)

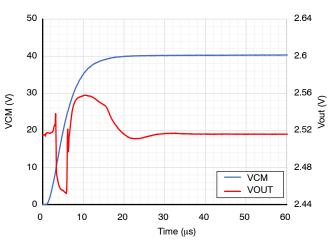
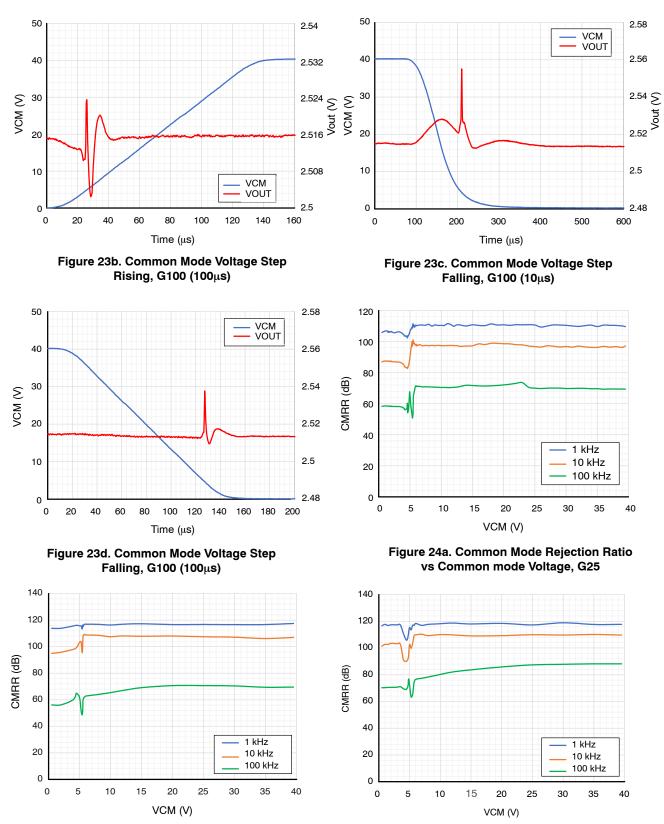


Figure 23a. Common Mode Voltage Step Rising, G100 (10μs)

TYPICAL CHARACTERISTICS (At $T_A = +25^{\circ}C$, $V_{SENSE} = (V_{IN+}) - (V_{IN-})$.; $V_S = V_{EN} = 1.8$ V, $V_{REF} = V_S/2$, $V_{CM} = 12$ V, and all gains unless otherwise noted.) (continued)



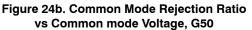
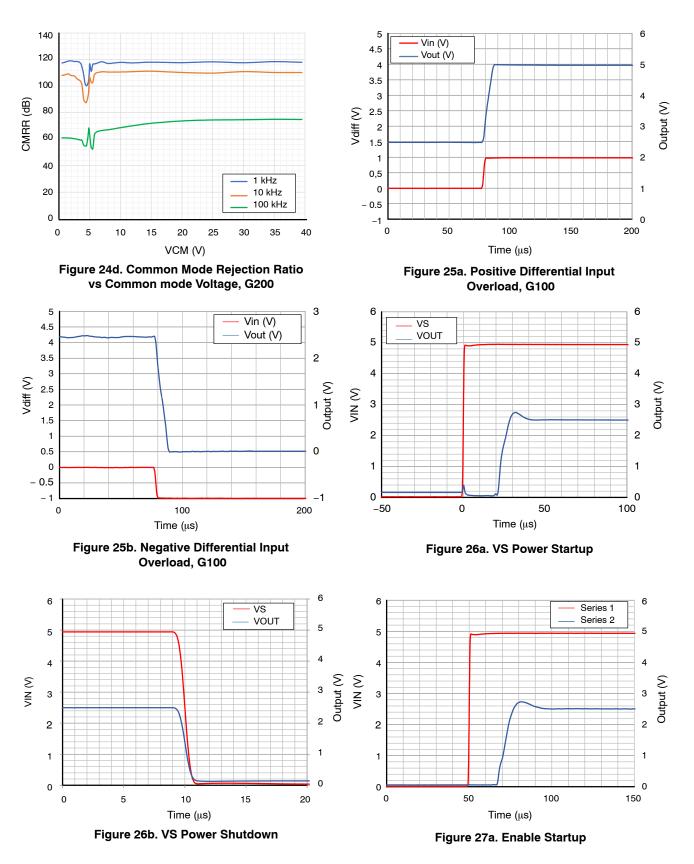


Figure 24c. Common Mode Rejection Ratio vs Common mode Voltage, G100



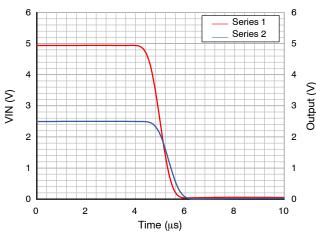


Figure 27b. Enable Shutdown

APPLICATION INFORMATION

Current Sensing Techniques

The NCS21671 and NCV21671 are current sense amplifiers featuring a wide common mode voltage range that spans from -0.1 V to 40 V independent of the supply voltage. These amplifiers can be configured for low-side and high-side current sensing.

At first glance, low-side sensing appears to have the advantage of being straightforward, inexpensive, and the ability to be implemented with a simple op amp circuit. However, the NCS21671 provides the full differential input necessary to get accurate shunt connections while also providing a built-in gain network with precision difficult to obtain with external resistors.

While at times the application requires low-side sensing, only high-side sensing can detect a short from the positive supply line to ground. Furthermore, high-side sensing avoids adding resistance to the ground path of the load being measured.

Bidirectional Operation

The NCS21671 can be configured to monitor unidirectional or bidirectional current flow.

In unidirectional current sensing, the measured load current always flows in the same direction. Common applications for unidirectional operation include power supplies and load current monitoring. The NCS21671 can be set up for unidirectional monitoring by connecting the REF pin to ground. In this configuration, the IN+ pin should be connected to the high side of the sense resistor, while the IN– pin should be connected to the low side of the sense resistor.

Bidirectional current sensing measures current flow in both directions. A common application for bidirectional current sensing is battery monitoring. While the battery is charging, current flows in one direction; while the battery is being used, current flows in the other direction. For bidirectional current flow, the REF pin can be connected to a voltage between GND and the Vs supply. Typically, the REF pin is connected to the mid-supply voltage for bidirectional monitoring.

Enable Pin

The enable pin can be used to shut down the part and reduce current consumption. When the part is shut down, quiescent current drops to less than 1 μ A and the inputs become high impedance. The output also becomes high impedance in the shutdown mode.

Input Filtering

Some applications may require filtering at the input of the current sense amplifier. Input filtering is simplified with the CIN+ and CIN- pins. Simply add an external capacitor across the pins to set the cutoff frequency, f_c .

$$f_{c} = \frac{1}{2\pi (2R_{Filt})C_{Filt}}$$
(eq. 1)

Table 1. Internal Resistance Values

| Gain (V/V) | R _{filt} (kΩ) | R _{in} (kΩ) | R _{fb} (MΩ) |
|------------|------------------------|----------------------|----------------------|
| 25 | 20 | 20 | 1 |
| 50 | 10 | 10 | 1 |
| 100 | 5 | 5 | 1 |
| 200 | 2.5 | 2.5 | 1 |

The internal filter resistance has a tolerance of $\pm 25\%$.

If the filtering capacitor is not used, Cin+ and Cin- pins should be left floating.

As shunt resistors decrease in value, shunt inductance can significantly affect frequency response. At values below 1 m Ω , the shunt inductance causes a zero in the transfer function that often results in corner frequencies in the low 100's of kHz. This inductance increases the amplitude of high frequency spike transient events on the current sensing

line that can overload the front end of any shunt current sensing IC.

This problem must be solved by filtering at the input of the amplifier. Note that all current sensing ICs are vulnerable to this problem, regardless of manufacturer claims. Filtering is required at the input of the device to resolve this problem, even if the spike frequencies are above the rated bandwidth of the device.

Ideally, select the capacitor to exactly match the time constant of the shunt resistor and its inductance; alternatively, select the capacitor to provide a pole below that point. Make the input filter time constant equal to or larger than the shunt and its inductance time constant:

$$\frac{L_{SHUNT}}{R_{SHUNT}} \le R_{FILT}C_{FILT}$$
 (eq. 2)

Selecting the Shunt Resistor

The desired accuracy of the current measurement determines the precision, shunt size, and the resistor value. The larger the resistor value, the more accurate the measurement possible, but a large resistor value also results in greater current loss. For the most accurate measurements, use four terminal current sense resistors. It provides two terminals for the current path in the application circuit, and a second pair for the voltage detection path of the sense amplifier. This technique is also known as *Kelvin Sensing*. This ensures that the voltage measured by the sense amplifier is the actual voltage across the resistor and does not include the small resistance of a combined connection. When using non-Kelvin shunts, follow manufacturer recommendations on how to lay out the sensing traces closely.

Gain Options

The gain is set by integrated, precision, ratio-matched resistors. The NCS21671 is available in gain options of 25 V/V, 50 V/V, 100 V/V, and 200 V/V. Adding external resistors to adjust the gain can contribute to the overall system error and is not recommended.

$$P_{D} \approx V_{in}(I_{GND}@I_{out}) + I_{out}(V_{in} - V_{out})$$
 (eq. 3)

$$V_{in(MAX)} \approx \frac{P_{D(MAX)} + (V_{out} \cdot I_{out})}{I_{out} + I_{GND}} \eqno(eq. 4)$$

ORDERING INFORMATION

| Device | Channels | Package | Gain | OPN | Marking | Shipping [†] |
|--------------|----------|---------|----------------|------------------|---------|-----------------------|
| INDUSTRIAL A | | | | | | |
| Package | GAIN | Enable | Filter Pins | Part Number | Marking | Shipping |
| SC70-6 | 25 | No | No | NCS21671SQ025T2G | AAC(M) | Tape and Reel |
| | 50 | | | NCS21671SQ050T2G | \A/(YW) | 3000 / Reel |
| | 100 | | | NCS21671SQ100T2G | \A/(YW) | |
| | 200 | 1 | | NCS21671SQ200T2G | R(YW) | |
| Micro10 | 25 | Yes | Yes | NCS21671DM025R2G | G025 | Tape and Reel |
| | 50 | | | NCS21671DM050R2G | G050 | 4000 / Reel |
| | 100 |] | | NCS21671DM100R2G | G100 |] |
| | 200 | 1 | | NCS21671DM200R2G | G200 | 1 |

AUTOMOTIVE GRADE1 QUALIFIED

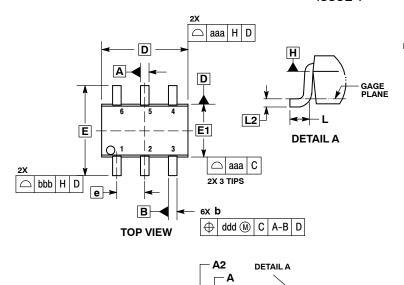
| Package | GAIN | Enable | Filter Pins | Part Number | Marking | Shipping |
|---------|------|--------|----------------|------------------|---------|---------------|
| SC70-6 | 25 | No | No | NCV21671SQ025T2G | AAC(M) | Tape and Reel |
| | 50 | | | NCV21671SQ050T2G | \A/(YW) | 3000 / Reel |
| | 100 | 1 | | NCV21671SQ100T2G | \A/(YW) | |
| | 200 | 1 | | NCV21671SQ200T2G | R(YW) | |
| Micro10 | 25 | Yes | Yes | NCV21671DM025R2G | G025 | Tape and Reel |
| | 50 | 1 | | NCV21671DM050R2G | G050 | 4000 / Reel |
| | 100 | | | NCV21671DM100R2G | G100 | |
| | 200 | | | NCV21671DM200R2G | G200 | |

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, <u>BRD8011/D</u>.

*NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

PACKAGE DIMENSIONS

SC-88/SC70-6/SOT-363 CASE 419B-02 **ISSUE Y**



NOTES:

С

END VIEW

- 1. 2.
- З.
- ITES: DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRU-SIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H. DATUMS A AND B ARE DETERMINED AT DATUM H. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP. DIMENSION b DORS NOT INCLUDE DAMBAR PROTRUISION 4
- 5. 6.
- 7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION 6 AT MAXIMUM MATERIAL CONDI-TION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

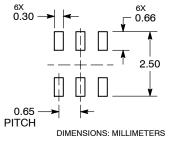
| | MILLIMETERS | | | INCHES | | | |
|-----|-------------|----------|------|-----------|-----------|-------|--|
| DIM | MIN | NOM | MAX | MIN | NOM | MAX | |
| Α | | | 1.10 | | | 0.043 | |
| A1 | 0.00 | | 0.10 | 0.000 | | 0.004 | |
| A2 | 0.70 | 0.90 | 1.00 | 0.027 | 0.035 | 0.039 | |
| b | 0.15 | 0.20 | 0.25 | 0.006 | 0.008 | 0.010 | |
| С | 0.08 | 0.15 | 0.22 | 0.003 | 0.006 | 0.009 | |
| D | 1.80 | 2.00 | 2.20 | 0.070 | 0.078 | 0.086 | |
| E | 2.00 | 2.10 | 2.20 | 0.078 | 0.082 | 0.086 | |
| E1 | 1.15 | 1.25 | 1.35 | 0.045 | 0.049 | 0.053 | |
| е | (| 0.65 BS | С | 0.026 BSC | | | |
| L | 0.26 | 0.36 | 0.46 | 0.010 | 0.014 | 0.018 | |
| L2 | | 0.15 BSC | | | 0.006 BSC | | |
| aaa | | 0.15 | | | 0.006 | | |
| bbb | | 0.30 | | | 0.012 | | |
| ccc | | 0.10 | | | 0.004 | | |
| ddd | | 0.10 | | | 0.004 | | |

RECOMMENDED **SOLDERING FOOTPRINT***

SIDE VIEW

A1

ex ◯ ccc C



*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

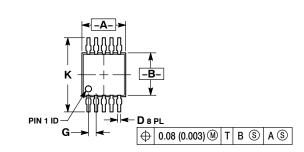
STYLES ON PAGE 2

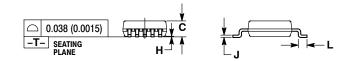
SC-88/SC70-6/SOT-363 CASE 419B-02 ISSUE Y

| STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2 | STYLE 2: CANCELLED | STYLE 3: CANCELLED | STYLE 4: PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE | STYLE 5: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE | STYLE 6: PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2 |
|--|-----------------------|--|---|---|---|
| STYLE 7: PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2 | STYLE 8: CANCELLED | STYLE 9: PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2 | STYLE 10: PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2 | STYLE 11: PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2 | STYLE 12: PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2 |
| STYLE 13: | STYLE 14: | STYLE 15: | STYLE 16: | STYLE 17: | STYLE 18: |
| PIN 1. ANODE | PIN 1. VREF | PIN 1. ANODE 1 | PIN 1. BASE 1 | PIN 1. BASE 1 | PIN 1. VIN1 |
| 2. N/C | 2. GND | 2. ANODE 2 | 2. EMITTER 2 | 2. EMITTER 1 | 2. VCC |
| 3. COLLECTOR | 3. GND | 3. ANODE 3 | 3. COLLECTOR 2 | 3. COLLECTOR 2 | 3. VOUT2 |
| 4. EMITTER | 4. IOUT | 4. CATHODE 3 | 4. BASE 2 | 4. BASE 2 | 4. VIN2 |
| 5. BASE | 5. VEN | 5. CATHODE 2 | 5. EMITTER 1 | 5. EMITTER 2 | 5. GND |
| 6. CATHODE | 6. VCC | 6. CATHODE 1 | 6. COLLECTOR 1 | 6. COLLECTOR 1 | 6. VOUT1 |
| STYLE 19: | STYLE 20: | STYLE 21: | STYLE 22: | STYLE 23: | STYLE 24: |
| PIN 1. I OUT | PIN 1. COLLECTOR | PIN 1. ANODE 1 | PIN 1. D1 (i) | PIN 1. Vn | PIN 1. CATHODE |
| 2. GND | 2. COLLECTOR | 2. N/C | 2. GND | 2. CH1 | 2. ANODE |
| 3. GND | 3. BASE | 3. ANODE 2 | 3. D2 (i) | 3. Vp | 3. CATHODE |
| 4. V CC | 4. EMITTER | 4. CATHODE 2 | 4. D2 (c) | 4. N/C | 4. CATHODE |
| 5. V EN | 5. COLLECTOR | 5. N/C | 5. VBUS | 5. CH2 | 5. CATHODE |
| 6. V REF | 6. COLLECTOR | 6. CATHODE 1 | 6. D1 (c) | 6. N/C | 6. CATHODE |
| STYLE 25: | STYLE 26: | STYLE 27: | STYLE 28: | STYLE 29: | STYLE 30: |
| PIN 1. BASE 1 | PIN 1. SOURCE 1 | PIN 1. BASE 2 | PIN 1. DRAIN | PIN 1. ANODE | PIN 1. SOURCE 1 |
| 2. CATHODE | 2. GATE 1 | 2. BASE 1 | 2. DRAIN | 2. ANODE | 2. DRAIN 2 |
| 3. COLLECTOR 2 | 3. DRAIN 2 | 3. COLLECTOR 1 | 3. GATE | 3. COLLECTOR | 3. DRAIN 2 |
| 4. BASE 2 | 4. SOURCE 2 | 4. EMITTER 1 | 4. SOURCE | 4. EMITTER | 4. SOURCE 2 |
| 5. EMITTER | 5. GATE 2 | 5. EMITTER 2 | 5. DRAIN | 5. BASE/ANODE | 5. GATE 1 |
| 6. COLLECTOR 1 | 6. DRAIN 1 | 6. COLLECTOR 2 | 6. DRAIN | 6. CATHODE | 6. DRAIN 1 |

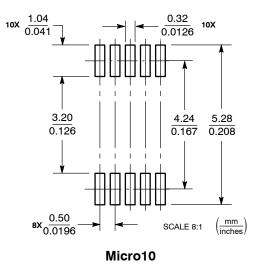
Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

Micro10 CASE 846B-03 ISSUE D





SOLDERING FOOTPRINT



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NOTES:

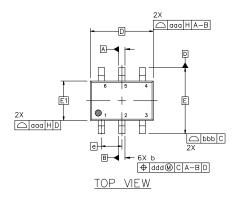
- 1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER. DIMENSION "A" DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- DIMENSION "B" DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION 4. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- 5 846B-01 OBSOLETE. NEW STANDARD 846B-02

| | MILLIN | IETERS | INCHES | | |
|-----|--------|--------|-----------|-------|--|
| DIM | MIN | MAX | MIN | MAX | |
| Α | 2.90 | 3.10 | 0.114 | 0.122 | |
| В | 2.90 | 3.10 | 0.114 | 0.122 | |
| C | 0.95 | 1.10 | 0.037 | 0.043 | |
| D | 0.20 | 0.30 | 0.008 | 0.012 | |
| G | 0.50 | BSC | 0.020 BSC | | |
| Н | 0.05 | 0.15 | 0.002 | 0.006 | |
| ſ | 0.10 | 0.21 | 0.004 | 0.008 | |
| Κ | 4.75 | 5.05 | 0.187 | 0.199 | |
| L | 0.40 | 0.70 | 0.016 | 0.028 | |

semi

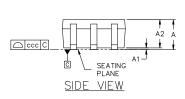
SC-88 2.00x1.25x0.90, 0.65P CASE 419B-02 **ISSUE Z**

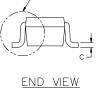
DATE 18 APR 2024



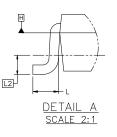


- DIMENSIONING AND TOLERANCING CONFORM TO ASME 1. Y14.5-2018.
- 2.
- ALL DIMENSION ARE IN MILLIMETERS. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 3. PER END.
- 4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF
- DATUMS A AND B ARE DETERMINED AT DATUM H. 5.
- DIMENSIONS & AND C APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP. 6.
- DIMENSION & DOES NOT INCLUDE DAMBAR PROTRUSION. 7 ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION & AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.





DETAIL A



| | MILLIMETERS | | | |
|-----|-------------|----------|------|--|
| DIM | MIN. | NOM. | MAX. | |
| A | | | 1.10 | |
| A1 | 0.00 | | 0.10 | |
| A2 | 0.70 | 0.90 | 1.00 | |
| b | 0.15 | 0.20 | 0.25 | |
| С | 0.08 | 0.15 | 0.22 | |
| D | 2.00 BSC | | | |
| E | 2.10 BSC | | | |
| E1 | 1.25 BSC | | | |
| е | | 0.65 BSC |) | |
| L | 0.26 | 0.36 | 0.46 | |
| L2 | 0.15 BSC | | | |
| aaa | 0.15 | | | |
| bbb | 0.30 | | | |
| ссс | 0.10 | | | |
| ddd | | 0.10 | | |

6X 0.66 6X 0.30-2.50 0.65 PITCH

RECOMMENDED MOUNTING FOOTPRINT*

FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

XXX = Specific Device Code = Date Code* Μ

GENERIC **MARKING DIAGRAM***

XXXM-

. 0

6

= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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|--|--|--|-------------|--|--|--|
| DESCRIPTION: | SC-88 2.00x1.25x0.90, 0.65P | | PAGE 1 OF 2 | | | |
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SC-88 2.00x1.25x0.90, 0.65P CASE 419B-02 ISSUE Z

DATE 18 APR 2024

| STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2 | STYLE 2: CANCELLED | STYLE 3: CANCELLED | STYLE 4: PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE | STYLE 5: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE | STYLE 6: PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2 |
|--|-----------------------|--|---|---|---|
| STYLE 7: PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2 | STYLE 8: CANCELLED | STYLE 9: PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2 | STYLE 10: PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2 | STYLE 11: PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2 | STYLE 12: PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2 |
| STYLE 13: | STYLE 14: | STYLE 15: | STYLE 16: | STYLE 17: | STYLE 18: |
| PIN 1. ANODE | PIN 1. VREF | PIN 1. ANODE 1 | PIN 1. BASE 1 | PIN 1. BASE 1 | PIN 1. VIN1 |
| 2. N/C | 2. GND | 2. ANODE 2 | 2. EMITTER 2 | 2. EMITTER 1 | 2. VCC |
| 3. COLLECTOR | 3. GND | 3. ANODE 3 | 3. COLLECTOR 2 | 3. COLLECTOR 2 | 3. VOUT2 |
| 4. EMITTER | 4. IOUT | 4. CATHODE 3 | 4. BASE 2 | 4. BASE 2 | 4. VIN2 |
| 5. BASE | 5. VEN | 5. CATHODE 2 | 5. EMITTER 1 | 5. EMITTER 2 | 5. GND |
| 6. CATHODE | 6. VCC | 6. CATHODE 1 | 6. COLLECTOR 1 | 6. COLLECTOR 1 | 6. VOUT1 |
| STYLE 19: | STYLE 20: | STYLE 21: | STYLE 22: | STYLE 23: | STYLE 24: |
| PIN 1. I OUT | PIN 1. COLLECTOR | PIN 1. ANODE 1 | PIN 1. D1 (i) | PIN 1. Vn | PIN 1. CATHODE |
| 2. GND | 2. COLLECTOR | 2. N/C | 2. GND | 2. CH1 | 2. ANODE |
| 3. GND | 3. BASE | 3. ANODE 2 | 3. D2 (i) | 3. Vp | 3. CATHODE |
| 4. V CC | 4. EMITTER | 4. CATHODE 2 | 4. D2 (c) | 4. N/C | 4. CATHODE |
| 5. V EN | 5. COLLECTOR | 5. N/C | 5. VBUS | 5. CH2 | 5. CATHODE |
| 6. V REF | 6. COLLECTOR | 6. CATHODE 1 | 6. D1 (c) | 6. N/C | 6. CATHODE |
| STYLE 25: | STYLE 26: | STYLE 27: | STYLE 28: | STYLE 29: | STYLE 30: |
| PIN 1. BASE 1 | PIN 1. SOURCE 1 | PIN 1. BASE 2 | PIN 1. DRAIN | PIN 1. ANODE | PIN 1. SOURCE 1 |
| 2. CATHODE | 2. GATE 1 | 2. BASE 1 | 2. DRAIN | 2. ANODE | 2. DRAIN 2 |
| 3. COLLECTOR 2 | 3. DRAIN 2 | 3. COLLECTOR 1 | 3. GATE | 3. COLLECTOR | 3. DRAIN 2 |
| 4. BASE 2 | 4. SOURCE 2 | 4. EMITTER 1 | 4. SOURCE | 4. EMITTER | 4. SOURCE 2 |
| 5. EMITTER | 5. GATE 2 | 5. EMITTER 2 | 5. DRAIN | 5. BASE/ANODE | 5. GATE 1 |
| 6. COLLECTOR 1 | 6. DRAIN 1 | 6. COLLECTOR 2 | 6. DRAIN | 6. CATHODE | 6. DRAIN 1 |

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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|------------------|---|--|-------------|--|--|--|
| DESCRIPTION: | SC-88 2.00x1.25x0.90, 0.65P | | PAGE 2 OF 2 | | | |
| | | | | | | |

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SCALE 2:1

Micro10 CASE 846B-03 ISSUE D

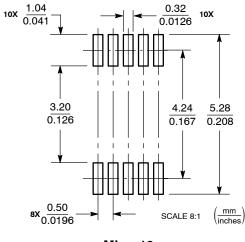
DATE 07 DEC 2004

DURSEM

< -A--B κ ឋឋኒ PIN 1 ID D 8 PL G ⊕ 0.08 (0.003) M T B S A S 0.038 (0.0015) \cap С -T-SEATING PLANE

SOLDERING FOOTPRINT

н



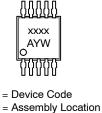
Micro10

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER. 3. DIMENSION "A" DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006)
- PER SIDE. 4. DIMENSION "B" DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
- SHALL NOT EXCEED 0.25 (0.010) PER SIDE. 5. 846B-01 OBSOLETE. NEW STANDARD 846B-02

| | MILLIMETERS | | INCHES | |
|-----|-------------|------|-----------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 2.90 | 3.10 | 0.114 | 0.122 |
| В | 2.90 | 3.10 | 0.114 | 0.122 |
| С | 0.95 | 1.10 | 0.037 | 0.043 |
| D | 0.20 | 0.30 | 0.008 | 0.012 |
| G | 0.50 | BSC | 0.020 BSC | |
| Н | 0.05 | 0.15 | 0.002 | 0.006 |
| J | 0.10 | 0.21 | 0.004 | 0.008 |
| K | 4.75 | 5.05 | 0.187 | 0.199 |
| L | 0.40 | 0.70 | 0.016 | 0.028 |

GENERIC **MARKING DIAGRAM***



- XXXX
 - = Year

А Y

W

.

- = Work Week
- = Pb-Free Package

*This information is generic. Please refer to

device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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